2024년 1월 26일(금), 09:00-10:45
Room G(201),2층

K. Memory (Design & Process Technology) 분과

[FG1-K] Process and Modeling of Memory

좌장: 성석강 마스터(삼성전자), 김시준 교수(강원대학교)

초청발표 FG1-K-1 09:00-09:30	Device Simulation of Phase-change and Resistive Memories by Modeling Mesoscale Behaviors of Active Materials Dongmyung Jung, Chanhoo Park, Yechan Kim, Hwanwook Lee, Sagar Khot, and Yongwoo Kwon Hongik University
FG1-K-2 09:30-09:45	Analysis of Conduction Mechanism and Stress-induced Dielectric Leakage Current in 1x-nm DRAM Cell Capacitor for Cryogenic Memory Operation Soohong Eo[1], Sangwon Lee[1], Jingyu Park[1], Seonhaeng Lee[2], and Dae Hwan Kim[1] [1]School of Electrical Engineering, Kookmin University, [2]Memory Division, Samsung Electronics Co., Ltd.
FG1-K-3 09:45-10:00	Realization of Ultra-Low Leakage Current (~10^{-18}A/μm) in CVD Grown Monolayer MoS_2 1T1C DRAM Using Semimetal Bismuth Contact Jisoo Seok[1], Jae Eun Seo[1], and Jiwon Chang[1, 2] [1]Department of Materials Science and Engineering, Yonsei University, [2]Department of System Semiconductor Engineering, Yonsei University
FG1-K-4 10:00-10:15	3D Stackable Vertical-Sensing Electrochemical Random-Access Memory Using AP-PECVD-Grown WS_2 Electrode for Neuromorphic Application Kyumin Lee[1], Seungkwon Hwang[1,2], Dongmin Kim[1], Jongwon Yoon[2], Jung-Dae Kwon[2], Yonghun Kim[2], and Hyunsang Hwang[1] [1]Center for Single Atom-based Semiconductor Device and the Department of Materials Science and Engineering, POSTECH, [2]Department of Energy and Electronic Materials, Nanosurface Materials Division, KIMS
FG1-K-5 10:15-10:30	Modeling the Valence Change Mechanism and Drift Behavior of Oxygen Vacancies in HfO_2-Based Interlayer Memristor: A Simulation Approach Eun Young Kim, Juseong Park, Woojoon Park, Woon Hyung Cheong, and Kyung Min Kim KAIST

FG1-K-6 10:30-10:45	Investigation of Hot Carrier Degradation of 1x-nm DRAM Peripheral PMOS Transistors for Cryogenic Memory Applications Ha Young Bang[1], Hee Jun Lee[1], Jingyu Park[1], Seonhaeng Lee[2], and Dae Hwan Kim[1] [1]School of Electrical Engineering, Kookmin University, [2]Memory Division, Samsung Electronics Co., Ltd.